



30V N-Channel Enhancement Mode MOSFET

Voltage

30 V

Current

55 A

Features

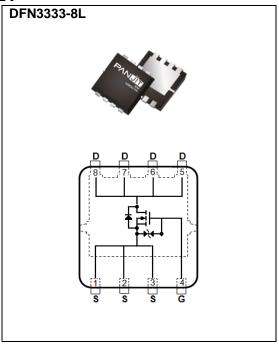
- RDS(ON), VGS@10V, ID@12A<6.5m Ω
- RDS(ON), VGS@4.5V, ID@9A<10.5m Ω
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETE	SYMBOL	LIMIT	UNITS		
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	v	
Continuous Drain Current ^(Note 3)	T _C =25°C	l _D	55	A	
	T _C =100°C		39		
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	220		
Power Dissipation	T _C =25°C	Po	32	W	
	T _C =100°C		16		
Continuous Drain Current(Note 4)	T _A =25°C		15.5		
	T _A =70°C	l _D	13	Α	
Power Dissipation	T _A =25°C	7	2.5	W	
	T _A =70°C	Po -	1.8		
Single Pulse Avalanche Energy ^(Note 5)		Eas	44	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Thermal Resistance ^(Note 4)	Junction to Case	$R_{ heta JC}$	4.7	°C/W	
	Junction to Ambient	$R_{\theta JA}$	60		





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30	-	-	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.2	1.76	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =12A	-	5.6	6.5	mΩ
		V _{GS} =4.5V, I _D =9A	-	8.3	10.5	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±10	uA
Dynamic ^(Note 6)						
Total Gate Charge	Q_g	V _{DS} =15V, I _D =12A, V _{GS} =10V ^(Note 2,3)	-	10.7	-	nC
Gate-Source Charge	Qgs		-	2	-	
Gate-Drain Charge	Q_{gd}		-	2.2	-	
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V, f=1MHz	-	785	-	pF
Output Capacitance	Coss		-	375	-	
Reverse Transfer Capacitance	Crss		-	25	-	
Gate resistance	Rg	f=1MHz	-	2	-	Ω
Turn-On Delay Time	td _(on)	V _{DS} =15V, I _D =1A, V _{GS} =10V, R _G =1Ω (Note 2,3)	-	6.5	-	ns
Turn-On Rise Time	tr		-	23	-	
Turn-Off Delay Time	td(off)		-	28	-	
Turn-Off Fall Time	tf		-	22	-	
Drain-Source Diode						
Diode Forward Current	Is	T _C =25°C	-	-	55	A
Pulsed Diode Forward Current	I _{SM}		-	-	220	
Diode Forward Voltage	V _{SD}	Is=10A, V _G s=0V	-	0.83	1.1	V
Reverse Recovery Time	Trr	V _{GS} =0V, I _S =10A	-	41	-	ns
Reverse Recovery Charge	Qrr	dls/dt=100A/us ^(Note 2,3)	-	22	-	nC

NOTES:

- 1. Pulse width<100us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an R_{eJC}=4.7°C/W.
- 4. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH, I_{AS}=13A, V_{DD}=30V, V_{GS}=10V, Starting TJ=25°C.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

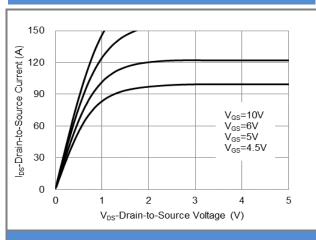


Fig.1 On-Region Characteristics

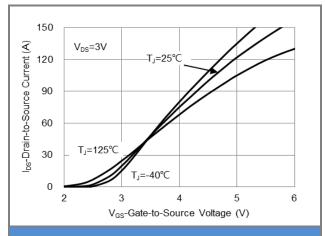


Fig.2 Transfer Characteristics

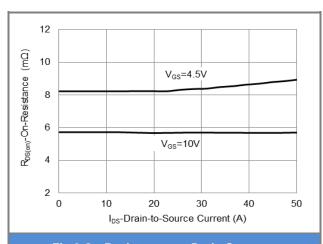


Fig.3 On-Resistance vs. Drain Current

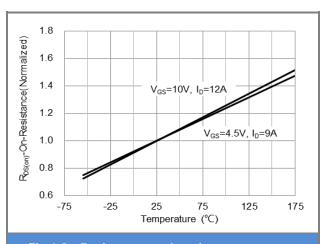


Fig.4 On-Resistance vs. Junction temperature

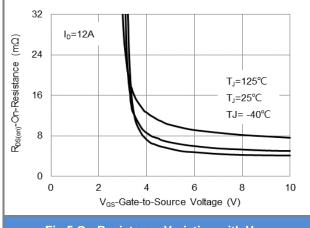


Fig.5 On-Resistance Variation with V_{GS}

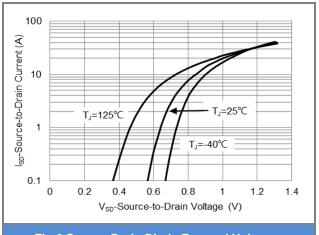


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

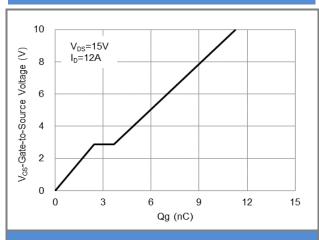


Fig.7 Gate-Charge Characteristics

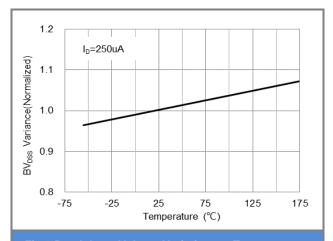


Fig.8 Breakdown Voltage Variation vs. Temperature

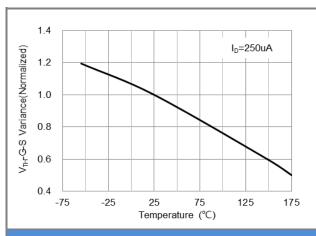


Fig.9 Threshold Voltage Variation with Temperature

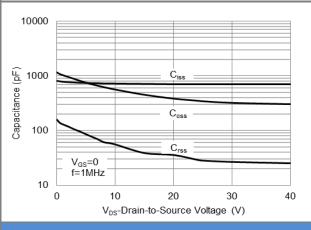


Fig.10 Capacitance vs. Drain-Source Voltage

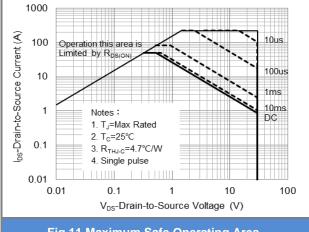


Fig.11 Maximum Safe Operating Area

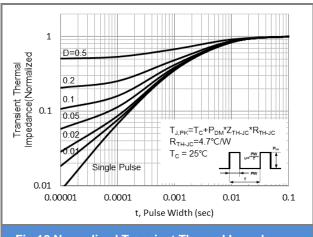


Fig.12 Normalized Transient Thermal Impedance

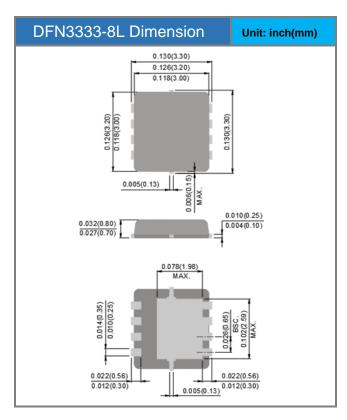


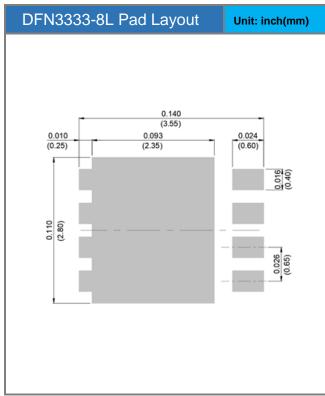


Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4528P-AU_R2_002A1	DFN3333-8L	5K pcs / 13" reel	4528	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout









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